Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	17358	collect\$4 adj region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2006/09/19 14:31
L2	849218	transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:16
L3	12474	1 and 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:18
L4	300143	emitter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:18
L5	11147	3 and 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:18
L6	61086	base adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:18
L7	1695	5 and 6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:19
L8	42655	gan or gallium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:19

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L9	66	L8 and 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:20
L10	41897	contact adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:20
L11	53	7 and 10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:36
L12	2	collect\$4 adj region and finger adj pitch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:38
L13	455	titanium/nickel or ti/ni	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:43
L14	1	7 and 13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:39
L15	462028	(titanium or ti) and (nickel or ni)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:43
L16	147	7 and 15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 16:41
L17	12	("4903104").URPN.	USPAT	OR	ON	2006/09/19 14:46

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L18	. 2	("4712121" "4739379").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/19 14:48
L19	1	collector near2 pad near10 (silicon adj nitride or sin or "si.sub.3.n.sub. 4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:37
L20	1	collector near4 pad near10 (silicon adj nitride or sin or "si.sub.3.n.sub. 4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:37
L21	20	collector near4 pad same (silicon adj nitride or sin or "si.sub.3.n.sub. 4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:42
L22	1912	438/149.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:41
L23	1247	collector near4 pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:43
L24	687	collector near2 pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:43
L25	1	22 and 24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:43
L27	1	22 and 23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:44

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L28	40	collect\$2 adj contact adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:58
L29	458	438/for.455.CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:59
L30	1	RF adj test adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 16:41
L31	4501	test adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 16:41
L32	1	22 and 31	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:14
L33	2245	438/14.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:15
L35	2203	contact adj pad near4 test\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:16
L36	54	33 and 35	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:16

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S1	40970	gan or gallium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 05:53
52	1500	hvpe or hydride adj vapor adj phase adj epitaxy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:38
S3	45306	sapphire	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 05:54
S4	113330	helium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 05:59
S5	49	S1 and S2 and S3 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 05:59
S6	3	(("3966501") or ("6410396") or ("6545340")).PN.	USPAT	OR	OFF	2006/06/14 06:48
S7	2	("20020177685").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/14 06:03
S8	14735	molecular adj beam adj epitaxy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:03
S9	35	S5 and S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:12

S11	4	(("3966501") or ("6410396") or ("6545340") or ("6533874")).PN.	USPAT	OR	OFF	2006/06/14 06:50
S12	32856	lift adj off or lift-off	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 15:34
S13	152	438/92.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:52
S14	362	438/312.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:52
S15	117	438/347.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:55
S16	1174	438/514.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:55
S17	125	438/520.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:55
S18	452	438/528.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:55
S19	200	permeable adj base adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:37

S20		S1 and S3 and S19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:56
S21	35990	lift adj off or liftoff	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:37
S22	845798	transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:43
S23	6243	S21 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:44
S24	42342	gan or gallium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:44
S25	1595	hvpe or hydride adj vapor adj phase adj epitaxy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:44
S26	1379	S24 and S25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:54
S27	102	S23 and S26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON ·	2006/08/31 08:44

S28	299358	emitter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:54
S29	1832566	collect\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:55
S30	172218	S28 and S29	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:55
S31	35	S26 and S30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:55
S32	5000895	base	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:55
S33	150530	S30 and S32	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:56
S34	27	S31 and S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:56
S35	4	(("3966501") or ("6410396") or ("6545340") or ("6533874")).PN.	USPAT	OR	OFF	2006/08/31 15:34
S36	33574	lift adj off or lift-off	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 15:34

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S37	1	S35 and S36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 15:34
S38	13	("4144116" "4622093" "4727047" "4888303" "4931132" "5210051" "5393993" "5679152" "5679965" "5777350" "5810925" "5874747" "5923946").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/08/31 15:48
S39	2	S36 and S38	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 15:48
S40	3	etch\$3 near5 base adj layer and (decreas\$3 or rampdown or ramp adj down or ramp-down) near7 bias adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:08
S41	3	etch\$3 near7 base adj layer and (decreas\$3 or rampdown or ramp adj down or ramp-down) near7 bias adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:08
S42	1697	(decreas\$3 or rampdown or ramp adj down or ramp-down) near7 bias adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:08
S44	307	etch\$3 and S42	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:00
S45	20	"n+ GaN layer" and "n- GaN layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:37

S46	66	(he or helium) adj (implantation or implant\$4) near7 (layer or liner or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:55
S47	0	(he or helium) adj (implantation or implant\$4) near7 "n+" adj (layer or liner or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:38
S48	78	(he or helium) adj (implantation or implant\$4) near12 (layer or liner or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:57
S49	12	S48 not S46	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 11:18
S50	919	(he or helium) near7 (implantation or implant\$4) same (layer or liner or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:58
S51	107	(he or helium) near7 (implantation or implant\$4) same insulat\$4 adj (layer or liner or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:58
S52	29	("5929467").URPN.	USPAT	OR	ON	2006/09/19 11:11
S53	3	"2000068605"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 11:19
S54	2	"6156581".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:11

S55	88	(ebeam or electronic adj beam) adj lithography	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:22
S57	130	438/520.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:26
S58	463	438/528.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:26
S59	824	438/597.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:39
S60	94	etch\$3 adj grooved	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:41
S61	36161	liftoff or lift adj off or lift-off	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:50
S62	238005	metal adj (layer or liner or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:51
S63	1003	S61 near5 S62	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:55

S67	216959	ebeam or e-beam or e adj beam or electron adj beam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:55
S68	277	S63 and S67	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:16

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